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Group Art Unit: 2814

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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s)	Katsumi Sameshima	Examiner:	Wai-Sing Louie
Serial No.:	09/451,979	Group Art Unit:	2814
Confirmation No.:	Unassigned	Docket:	362-39
Filed:	November 30, 1999	Dated:	February 13, 2002
For:	FERROELECTRIC MEMORY AND METHOD FOR MANUFACTURING SAME		

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DRAFT PROPOSED AMENDMENT

Sir:

In response to the final Office Action mailed October 19, 2001, a reply to which is due February 19, 2002 with a Petition for Extension of Time, the following amendments are proposed:

IN THE CLAIMS:

Please amend Claims 1 -5 by rewriting the same as follows:

1. (Twice Amended) A ferroelectric memory, comprising:
an insulation film having a [hollow] concave portion at a top surface; and
a laminated body obtained by laminating a plurality of layers on said top surface and etching a region of said plurality of layers corresponding to a region other than said [hollow] concave portion, wherein said laminated body includes a lower electrode layer which is brought into contact with a bottom surface of said concave portion, a ferroelectric layer formed on said lower electrode layer and an upper electrode layer formed on said ferroelectric layer, wherein a portion of said lower electrode layer protrudes outward from an